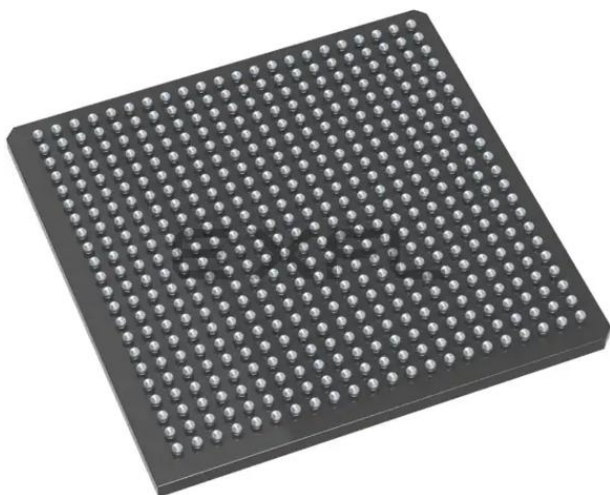




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

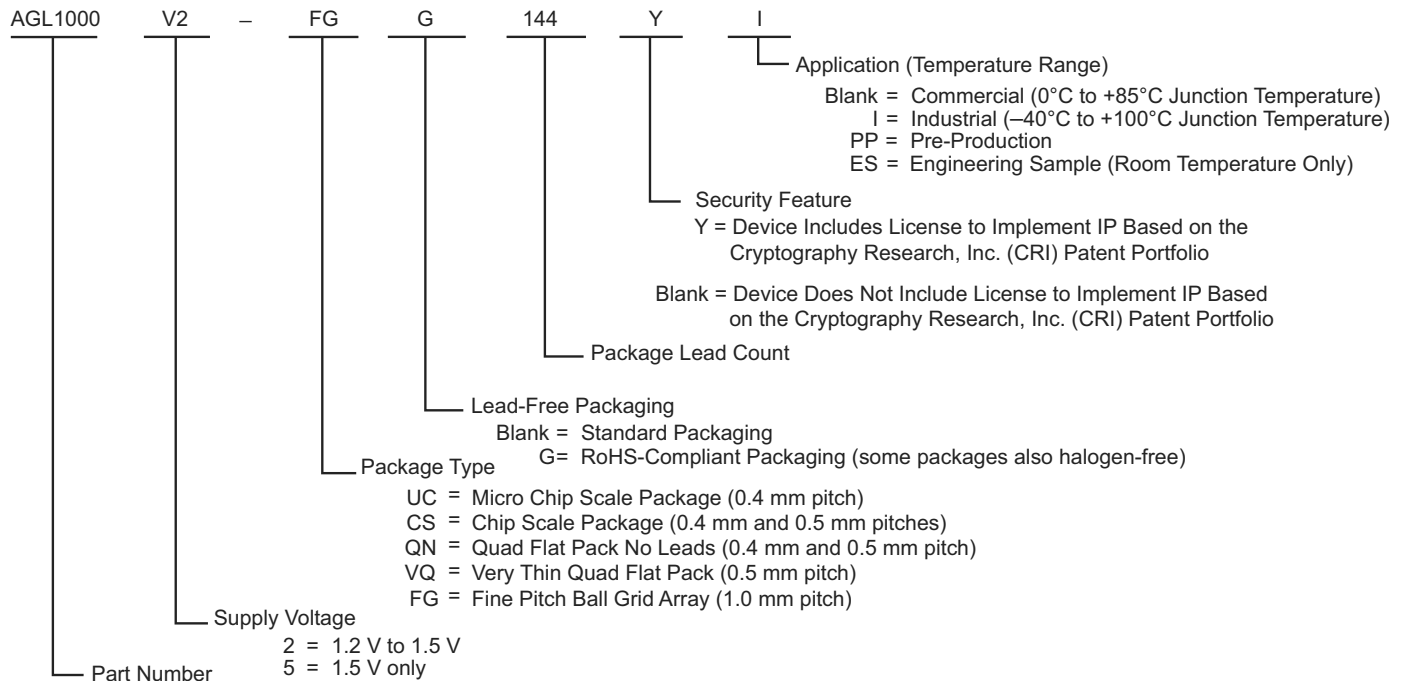
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	13824
Total RAM Bits	110592
Number of I/O	235
Number of Gates	600000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1agl600v5-fg484

IGLOO Ordering Information



IGLOO Devices

AGL015 = 15,000 System Gates
AGL030 = 30,000 System Gates
AGL060 = 60,000 System Gates
AGL125 = 125,000 System Gates
AGL250 = 250,000 System Gates
AGL400 = 400,000 System Gates
AGL600 = 600,000 System Gates
AGL1000 = 1,000,000 System Gates

IGLOO Devices with Cortex-M1

M1AGL250 = 250,000 System Gates
M1AGL600 = 600,000 System Gates
M1AGL1000 = 1,000,000 System Gates

Note: Marking Information: IGLOO V2 devices do not have V2 marking, but IGLOO V5 devices are marked accordingly.

Ramping up (V2 devices): $0.65\text{ V} < \text{trip_point_up} < 1.05\text{ V}$
 Ramping down (V2 devices): $0.55\text{ V} < \text{trip_point_down} < 0.95\text{ V}$

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLX exceed brownout activation levels (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels ($0.75\text{ V} \pm 0.25\text{ V}$ for V5 devices, and $0.75\text{ V} \pm 0.2\text{ V}$ for V2 devices), the PLL output lock signal goes low and/or the output clock is lost. Refer to the Brownout Voltage section in the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the ProASIC®3 and ProASIC3E FPGA fabric user guides for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

To make sure the transition from input buffers to output buffers is clean, ensure that there is no path longer than 100 ns from input buffer to output buffer in your design.

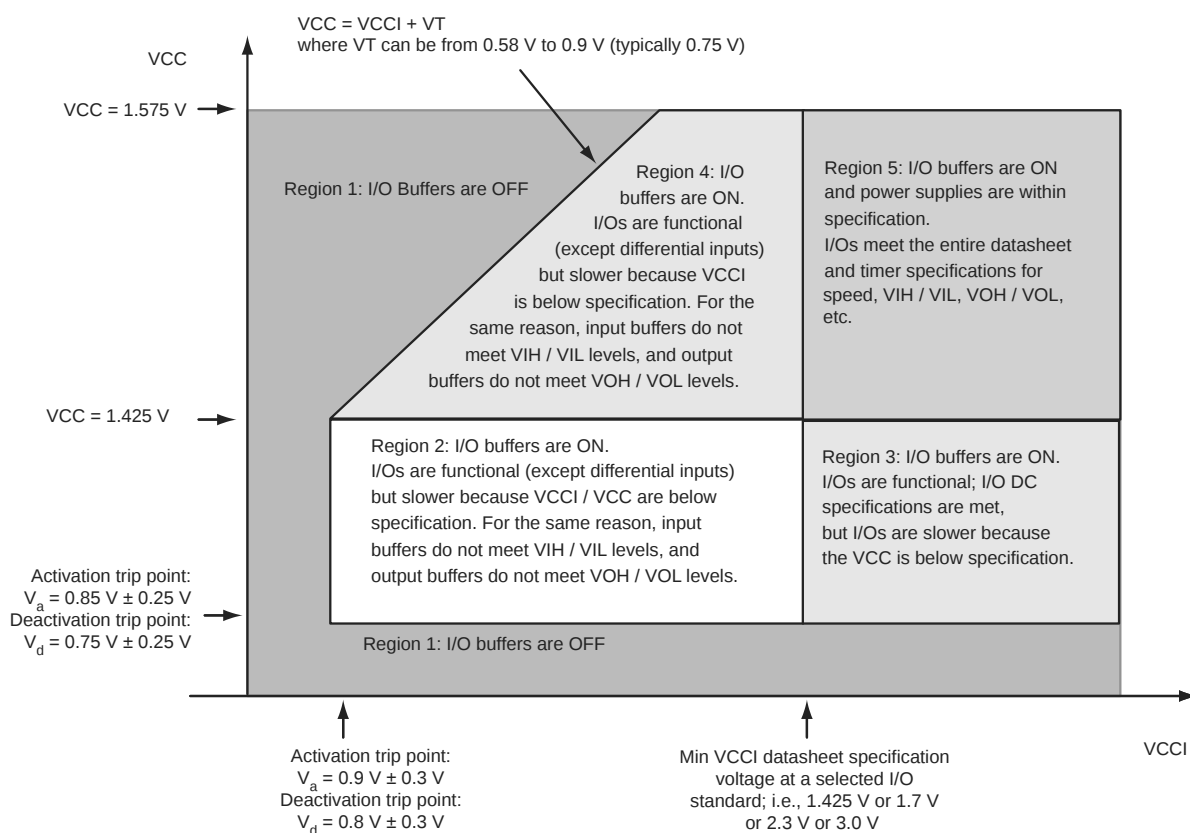


Figure 2-1 • V5 Devices – I/O State as a Function of VCCI and VCC Voltage Levels

**Table 2-28 • Summary of Maximum and Minimum DC Input Levels
Applicable to Commercial and Industrial Conditions**

DC I/O Standards	Commercial ¹		Industrial ²	
	IIL ⁴	IIH ⁵	IIL ⁴	IIH ⁵
	μA	μA	μA	μA
3.3 V LVTTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCMOS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
1.2 V LVCMOS ³	10	10	15	15
1.2 V LVCMOS Wide Range ³	10	10	15	15
3.3 V PCI	10	10	15	15
3.3 V PCI-X	10	10	15	15

Notes:

1. Commercial range ($0^{\circ}\text{C} < T_A < 70^{\circ}\text{C}$)
2. Industrial range ($-40^{\circ}\text{C} < T_A < 85^{\circ}\text{C}$)
3. Applicable to V2 Devices operating at $V_{CCI} \geq V_{CC}$.
4. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
5. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges

Timing Characteristics***Applies to 1.5 V DC Core Voltage***

Table 2-51 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	4.47	0.18	0.85	0.66	4.56	3.89	2.24	2.19	8.15	7.48	ns
4 mA	Std.	0.97	4.47	0.18	0.85	0.66	4.56	3.89	2.24	2.19	8.15	7.48	ns
6 mA	Std.	0.97	3.74	0.18	0.85	0.66	3.82	3.37	2.49	2.63	7.42	6.96	ns
8 mA	Std.	0.97	3.74	0.18	0.85	0.66	3.82	3.37	2.49	2.63	7.42	6.96	ns
12 mA	Std.	0.97	3.23	0.18	0.85	0.66	3.30	2.98	2.66	2.91	6.89	6.57	ns
16 mA	Std.	0.97	3.08	0.18	0.85	0.66	3.14	2.89	2.70	2.99	6.74	6.48	ns
24 mA	Std.	0.97	3.00	0.18	0.85	0.66	3.06	2.91	2.74	3.27	6.66	6.50	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-52 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.73	0.18	0.85	0.66	2.79	2.22	2.25	2.32	6.38	5.82	ns
4 mA	Std.	0.97	2.73	0.18	0.85	0.66	2.79	2.22	2.25	2.32	6.38	5.82	ns
6 mA	Std.	0.97	2.32	0.18	0.85	0.66	2.37	1.85	2.50	2.76	5.96	5.45	ns
8 mA	Std.	0.97	2.32	0.18	0.85	0.66	2.37	1.85	2.50	2.76	5.96	5.45	ns
12 mA	Std.	0.97	2.09	0.18	0.85	0.66	2.14	1.68	2.67	3.05	5.73	5.27	ns
16 mA	Std.	0.97	2.05	0.18	0.85	0.66	2.10	1.64	2.70	3.12	5.69	5.24	ns
24 mA	Std.	0.97	2.07	0.18	0.85	0.66	2.12	1.60	2.75	3.41	5.71	5.20	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-53 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	3.94	0.18	0.85	0.66	4.02	3.46	1.98	2.03	7.62	7.05	ns
4 mA	Std.	0.97	3.94	0.18	0.85	0.66	4.02	3.46	1.98	2.03	7.62	7.05	ns
6 mA	Std.	0.97	3.24	0.18	0.85	0.66	3.31	2.99	2.21	2.42	6.90	6.59	ns
8 mA	Std.	0.97	3.24	0.18	0.85	0.66	3.31	2.99	2.21	2.42	6.90	6.59	ns
12 mA	Std.	0.97	2.76	0.18	0.85	0.66	2.82	2.63	2.36	2.68	6.42	6.22	ns
16 mA	Std.	0.97	2.76	0.18	0.85	0.66	2.82	2.63	2.36	2.68	6.42	6.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

Table 2-79 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.7	1.7	2.7	0.7	1.7	2	2	16	18	10	10
4 mA	−0.3	0.7	1.7	2.7	0.7	1.7	4	4	16	18	10	10
6 mA	−0.3	0.7	1.7	2.7	0.7	1.7	6	6	32	37	10	10
8 mA	−0.3	0.7	1.7	2.7	0.7	1.7	8	8	32	37	10	10
12 mA	−0.3	0.7	1.7	2.7	0.7	1.7	12	12	65	74	10	10
16 mA	−0.3	0.7	1.7	2.7	0.7	1.7	16	16	83	87	10	10
24 mA	−0.3	0.7	1.7	2.7	0.7	1.7	24	24	169	124	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-80 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.7	1.7	2.7	0.7	1.7	2	2	16	18	10	10
4 mA	−0.3	0.7	1.7	2.7	0.7	1.7	4	4	16	18	10	10
6 mA	−0.3	0.7	1.7	2.7	0.7	1.7	6	6	32	37	10	10
8 mA	−0.3	0.7	1.7	2.7	0.7	1.7	8	8	32	37	10	10
12 mA	−0.3	0.7	1.7	2.7	0.7	1.7	12	12	65	74	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-123 • 1.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	6.43	0.26	1.27	1.10	6.54	5.95	2.82	2.83	12.32	11.74	ns
4 mA	Std.	1.55	5.59	0.26	1.27	1.10	5.68	5.27	3.07	3.27	11.47	11.05	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-124 • 1.5 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.02	0.26	1.27	1.10	3.07	2.81	2.82	2.92	8.85	8.59	ns
4 mA	Std.	1.55	2.68	0.26	1.27	1.10	2.72	2.39	3.07	3.37	8.50	8.18	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-125 • 1.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	6.35	0.26	1.22	1.10	6.46	5.93	2.40	2.46	ns

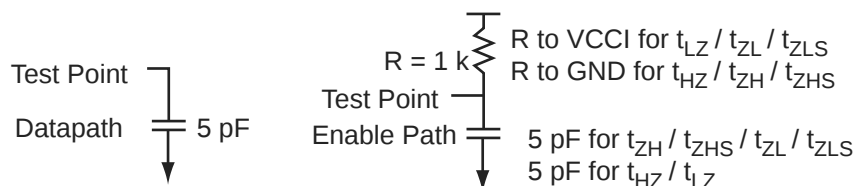
Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-126 • 1.5 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	2.92	0.26	1.22	1.10	2.96	2.60	2.40	2.56	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

**Figure 2-11 • AC Loading****Table 2-130 • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.2	0.6	5

Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.

Timing Characteristics

1.2 V DC Core Voltage

Table 2-131 • 1.2 V LVCMOS Low Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	8.37	0.26	1.60	1.10	8.04	7.17	3.94	3.52	13.82	12.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-132 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-133 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	7.59	0.26	1.59	1.10	7.29	6.54	3.30	3.35	13.08	12.33	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-134 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.59	1.10	3.11	2.78	3.29	3.48	8.90	8.57	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) and Multipoint LVDS (M-LVDS) specifications extend the existing LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The drivers require series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus since the driver can be located anywhere on the bus. These configurations can be implemented using the TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 2-14. The input and output buffer delays are available in the LVDS section in Table 2-149 on page 2-81 and Table 2-150 on page 2-81.

Example: For a bus consisting of 20 equidistant loads, the following terminations provide the required differential voltage, in worst-case Industrial operating conditions, at the farthest receiver: $R_S = 60\ \Omega$ and $R_T = 70\ \Omega$, given $Z_0 = 50\ \Omega$ (2") and $Z_{stub} = 50\ \Omega$ (~1.5").

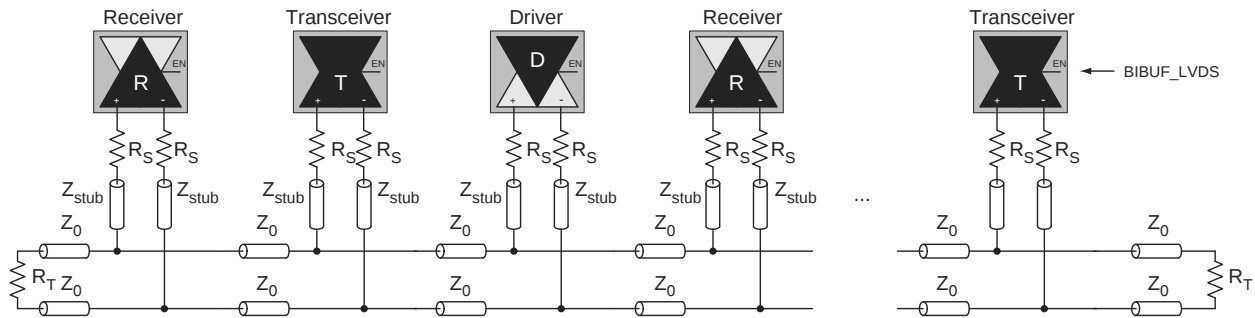


Figure 2-14 • B-LVDS/M-LVDS Multipoint Application Using LVDS I/O Buffers

LVPECL

Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Like LVDS, two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-15. The building blocks of the LVPECL transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVDS implementation because the output standard specifications are different.

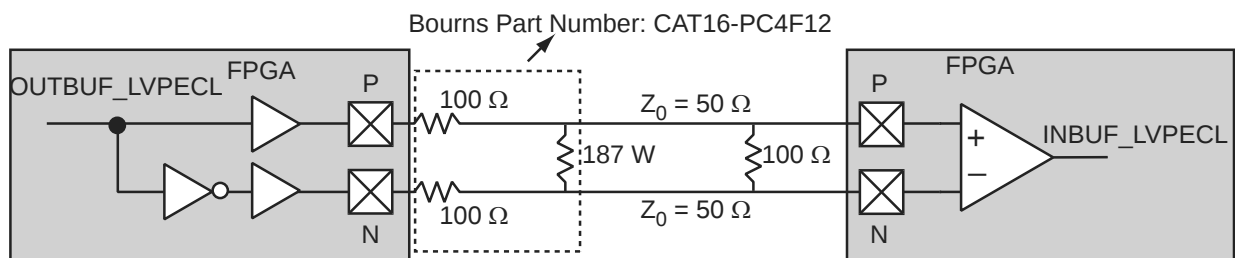


Figure 2-15 • LVPECL Circuit Diagram and Board-Level Implementation

Timing Characteristics

1.5 V DC Core Voltage

Table 2-169 • Combinatorial Cell Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Combinatorial Cell	Equation	Parameter	Std.	Units
INV	$Y = !A$	t_{PD}	0.80	ns
AND2	$Y = A \cdot B$	t_{PD}	0.84	ns
NAND2	$Y = !(A \cdot B)$	t_{PD}	0.90	ns
OR2	$Y = A + B$	t_{PD}	1.19	ns
NOR2	$Y = !(A + B)$	t_{PD}	1.10	ns
XOR2	$Y = A \oplus B$	t_{PD}	1.37	ns
MAJ3	$Y = \text{MAJ}(A, B, C)$	t_{PD}	1.33	ns
XOR3	$Y = A \oplus B \oplus C$	t_{PD}	1.79	ns
MUX2	$Y = A !S + B S$	t_{PD}	1.48	ns
AND3	$Y = A \cdot B \cdot C$	t_{PD}	1.21	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V DC Core Voltage

Table 2-170 • Combinatorial Cell Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$

Combinatorial Cell	Equation	Parameter	Std.	Units
INV	$Y = !A$	t_{PD}	1.34	ns
AND2	$Y = A \cdot B$	t_{PD}	1.43	ns
NAND2	$Y = !(A \cdot B)$	t_{PD}	1.59	ns
OR2	$Y = A + B$	t_{PD}	2.30	ns
NOR2	$Y = !(A + B)$	t_{PD}	2.07	ns
XOR2	$Y = A \oplus B$	t_{PD}	2.46	ns
MAJ3	$Y = \text{MAJ}(A, B, C)$	t_{PD}	2.46	ns
XOR3	$Y = A \oplus B \oplus C$	t_{PD}	3.12	ns
MUX2	$Y = A !S + B S$	t_{PD}	2.83	ns
AND3	$Y = A \cdot B \cdot C$	t_{PD}	2.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-190 • IGLOO CCC/PLL Specification
For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage

Parameter	Min.	Typ.	Max.	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		160	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		160	MHz
Delay Increments in Programmable Delay Blocks ^{1, 2}		580 ³		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Serial Clock (SCLK) for Dynamic PLL ^{4, 5}			60	ns
Input Cycle-to-Cycle Jitter (peak magnitude)			0.25	ns
Acquisition Time				
LockControl = 0			300	μs
LockControl = 1			6.0	ms
Tracking Jitter ⁶				
LockControl = 0			4	ns
LockControl = 1			3	ns
Output Duty Cycle	48.5		51.5	%
Delay Range in Block: Programmable Delay ^{1, 2}	2.3		20.86	ns
Delay Range in Block: Programmable Delay ^{2, 1, 2}	0.863		20.86	ns
Delay Range in Block: Fixed Delay ^{1, 2, 5}		5.7		ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT}	Maximum Peak-to-Peak Jitter Data ^{7, 8}			
	SSO ≥ 4 ⁹	SSO ≥ 8 ⁹	SSO ≥ 16 ⁹	
0.75 MHz to 50 MHz	1.20%	2.00%	3.00%	
50 MHz to 160 MHz	5.00%	7.00%	15.00%	

Notes:

1. This delay is a function of voltage and temperature. See Table 2-6 on page 2-7 and Table 2-7 on page 2-7 for deratings.
2. $T_J = 25^\circ\text{C}$, $V_{CC} = 1.2\text{ V}$
3. When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help associated with the core for more information.
4. Maximum value obtained for a Std. speed grade device in Worst-Case Commercial Conditions. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.
5. The AGL030 device does not support a PLL.
6. Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.
7. VCO output jitter is calculated as a percentage of the VCO frequency. The jitter (in ps) can be calculated by multiplying the VCO period by the per cent jitter. The VCO jitter (in ps) applies to CCC_OUT regardless of the output divider settings. For example, if the jitter on VCO is 300 ps, the jitter on CCC_OUT is also 300 ps, regardless of the output divider settings.
8. Measurements done with LVTTTL 3.3 V, 8 mA I/O drive strength, and high slew Rate. $V_{CC}/V_{CCPLL} = 1.14\text{ V}$, VQ/PQ/TQ type of packages, 20 pF load.
9. SSO are outputs that are synchronous to a single clock domain and have clock-to-out times that are within ±200 ps of each other. Switching I/Os are placed outside of the PLL bank. Refer to the "Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout" section in the IGLOO FPGA Fabric User Guide.
10. For definitions of Type 1 and Type 2, refer to the PLL Block Diagram in the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter of the IGLOO FPGA Fabric User Guide.

Embedded FlashROM Characteristics

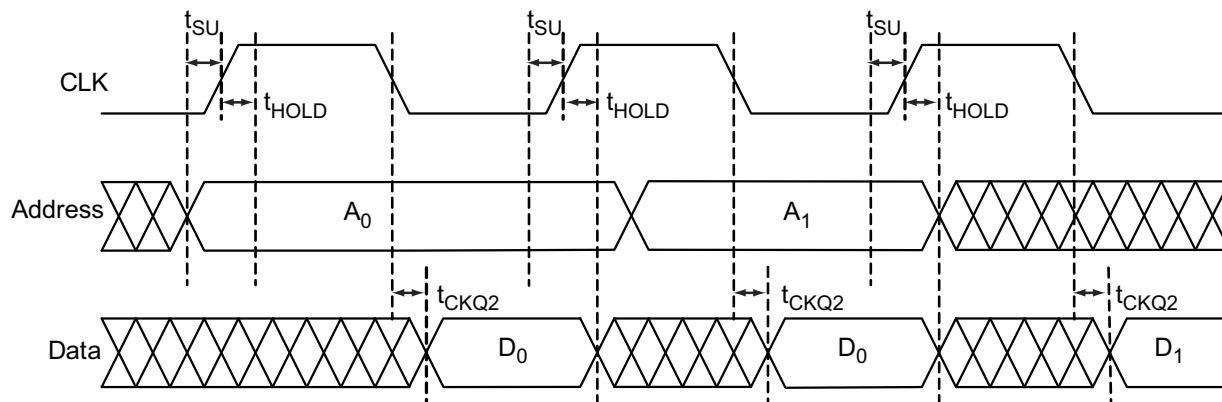


Figure 2-45 • Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-197 • Embedded FlashROM Access Time

Worst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.57	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	34.14	ns
F_{MAX}	Maximum Clock Frequency	15	MHz

1.2 V DC Core Voltage

Table 2-198 • Embedded FlashROM Access Time

Worst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.59	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	52.90	ns
F_{MAX}	Maximum Clock Frequency	10	MHz

UC81	
Pin Number	AGL030 Function
A1	IO00RSB0
A2	IO02RSB0
A3	IO06RSB0
A4	IO11RSB0
A5	IO16RSB0
A6	IO19RSB0
A7	IO22RSB0
A8	IO24RSB0
A9	IO26RSB0
B1	IO81RSB1
B2	IO04RSB0
B3	IO10RSB0
B4	IO13RSB0
B5	IO15RSB0
B6	IO20RSB0
B7	IO21RSB0
B8	IO28RSB0
B9	IO25RSB0
C1	IO79RSB1
C2	IO80RSB1
C3	IO08RSB0
C4	IO12RSB0
C5	IO17RSB0
C6	IO14RSB0
C7	IO18RSB0
C8	IO29RSB0
C9	IO27RSB0
D1	IO74RSB1
D2	IO76RSB1
D3	IO77RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	IO23RSB0
D8	IO31RSB0
D9	IO30RSB0

UC81	
Pin Number	AGL030 Function
E1	GEB0/IO71RSB1
E2	GEA0/IO72RSB1
E3	GEC0/IO73RSB1
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	GDC0/IO32RSB0
E8	GDA0/IO33RSB0
E9	GDB0/IO34RSB0
F1	IO68RSB1
F2	IO67RSB1
F3	IO64RSB1
F4	GND
F5	VCCIB1
F6	IO47RSB1
F7	IO36RSB0
F8	IO38RSB0
F9	IO40RSB0
G1	IO65RSB1
G2	IO66RSB1
G3	IO57RSB1
G4	IO53RSB1
G5	IO49RSB1
G6	IO45RSB1
G7	IO46RSB1
G8	VJTAG
G9	TRST
H1	IO62RSB1
H2	FF/IO60RSB1
H3	IO58RSB1
H4	IO54RSB1
H5	IO48RSB1
H6	IO43RSB1
H7	IO42RSB1
H8	TDI
H9	TDO

UC81	
Pin Number	AGL030 Function
J1	IO63RSB1
J2	IO61RSB1
J3	IO59RSB1
J4	IO56RSB1
J5	IO52RSB1
J6	IO44RSB1
J7	TCK
J8	TMS
J9	VPUMP

QN68	
Pin Number	AGL030 Function
1	IO82RSB1
2	IO80RSB1
3	IO78RSB1
4	IO76RSB1
5	GEC0/IO73RSB1
6	GEA0/IO72RSB1
7	GEB0/IO71RSB1
8	VCC
9	GND
10	VCCIB1
11	IO68RSB1
12	IO67RSB1
13	IO66RSB1
14	IO65RSB1
15	IO64RSB1
16	IO63RSB1
17	IO62RSB1
18	FF/IO60RSB1
19	IO58RSB1
20	IO56RSB1
21	IO54RSB1
22	IO52RSB1
23	IO51RSB1
24	VCC
25	GND
26	VCCIB1
27	IO50RSB1
28	IO48RSB1
29	IO46RSB1
30	IO44RSB1
31	IO42RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP
36	TDO

QN68	
Pin Number	AGL030 Function
37	TRST
38	VJTAG
39	IO40RSB0
40	IO37RSB0
41	GDB0/IO34RSB0
42	GDA0/IO33RSB0
43	GDC0/IO32RSB0
44	VCCIB0
45	GND
46	VCC
47	IO31RSB0
48	IO29RSB0
49	IO28RSB0
50	IO27RSB0
51	IO25RSB0
52	IO24RSB0
53	IO22RSB0
54	IO21RSB0
55	IO19RSB0
56	IO17RSB0
57	IO15RSB0
58	IO14RSB0
59	VCCIB0
60	GND
61	VCC
62	IO12RSB0
63	IO10RSB0
64	IO08RSB0
65	IO06RSB0
66	IO04RSB0
67	IO02RSB0
68	IO00RSB0

FG256	
Pin Number	AGL1000 Function
R5	IO168RSB2
R6	IO163RSB2
R7	IO157RSB2
R8	IO149RSB2
R9	IO143RSB2
R10	IO138RSB2
R11	IO131RSB2
R12	IO125RSB2
R13	GDB2/IO115RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO183RSB2
T3	FF/GEB2/IO186RSB2
T4	IO172RSB2
T5	IO170RSB2
T6	IO164RSB2
T7	IO158RSB2
T8	IO153RSB2
T9	IO142RSB2
T10	IO135RSB2
T11	IO130RSB2
T12	GDC2/IO116RSB2
T13	IO120RSB2
T14	GDA2/IO114RSB2
T15	TMS
T16	GND

FG484	
Pin Number	AGL400 Function
N17	IO74RSB1
N18	IO72NPB1
N19	IO70NDB1
N20	NC
N21	NC
N22	NC
P1	NC
P2	NC
P3	NC
P4	IO142NDB3
P5	IO141NPB3
P6	IO125RSB2
P7	IO139RSB3
P8	VCCIB3
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB1
P16	GDB0/IO78VPB1
P17	IO76VDB1
P18	IO76UDB1
P19	IO75PDB1
P20	NC
P21	NC
P22	NC
R1	NC
R2	NC
R3	VCC
R4	IO140PDB3
R5	IO130RSB2
R6	IO138NPB3
R7	GEC0/IO137NPB3
R8	VMV3

FG484	
Pin Number	AGL400 Function
U1	NC
U2	NC
U3	NC
U4	GEB1/IO136PDB3
U5	GEB0/IO136NDB3
U6	VMV2
U7	IO129RSB2
U8	IO128RSB2
U9	IO122RSB2
U10	IO115RSB2
U11	IO110RSB2
U12	IO98RSB2
U13	IO95RSB2
U14	IO88RSB2
U15	IO84RSB2
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO79VDB1
U20	NC
U21	NC
U22	NC
V1	NC
V2	NC
V3	GND
V4	GEA1/IO135PDB3
V5	GEA0/IO135NDB3
V6	IO127RSB2
V7	GEC2/IO132RSB2
V8	IO123RSB2
V9	IO118RSB2
V10	IO112RSB2
V11	IO106RSB2
V12	IO100RSB2
V13	IO96RSB2
V14	IO89RSB2

FG484	
Pin Number	AGL400 Function
Y7	NC
Y8	VCC
Y9	VCC
Y10	NC
Y11	NC
Y12	NC
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB1

FG484	
Pin Number	AGL1000 Function
B7	IO15RSB0
B8	IO19RSB0
B9	IO24RSB0
B10	IO31RSB0
B11	IO39RSB0
B12	IO48RSB0
B13	IO54RSB0
B14	IO58RSB0
B15	IO63RSB0
B16	IO66RSB0
B17	IO68RSB0
B18	IO70RSB0
B19	NC
B20	NC
B21	VCCIB1
B22	GND
C1	VCCIB3
C2	IO220PDB3
C3	NC
C4	NC
C5	GND
C6	IO10RSB0
C7	IO14RSB0
C8	VCC
C9	VCC
C10	IO30RSB0
C11	IO37RSB0
C12	IO43RSB0
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC

FG484	
Pin Number	AGL1000 Function
C21	NC
C22	VCCIB1
D1	IO219PDB3
D2	IO220NDB3
D3	NC
D4	GND
D5	GAA0/IO00RSB0
D6	GAA1/IO01RSB0
D7	GAB0/IO02RSB0
D8	IO16RSB0
D9	IO22RSB0
D10	IO28RSB0
D11	IO35RSB0
D12	IO45RSB0
D13	IO50RSB0
D14	IO55RSB0
D15	IO61RSB0
D16	GBB1/IO75RSB0
D17	GBA0/IO76RSB0
D18	GBA1/IO77RSB0
D19	GND
D20	NC
D21	NC
D22	NC
E1	IO219NDB3
E2	NC
E3	GND
E4	GAB2/IO224PDB3
E5	GAA2/IO225PDB3
E6	GNDQ
E7	GAB1/IO03RSB0
E8	IO17RSB0
E9	IO21RSB0
E10	IO27RSB0
E11	IO34RSB0
E12	IO44RSB0

FG484	
Pin Number	AGL1000 Function
E13	IO51RSB0
E14	IO57RSB0
E15	GBC1/IO73RSB0
E16	GBB0/IO74RSB0
E17	IO71RSB0
E18	GBA2/IO78PDB1
E19	IO81PDB1
E20	GND
E21	NC
E22	IO84PDB1
F1	NC
F2	IO215PDB3
F3	IO215NDB3
F4	IO224NDB3
F5	IO225NDB3
F6	VMV3
F7	IO11RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO25RSB0
F11	IO36RSB0
F12	IO42RSB0
F13	IO49RSB0
F14	IO56RSB0
F15	GBC0/IO72RSB0
F16	IO62RSB0
F17	VMV0
F18	IO78NDB1
F19	IO81NDB1
F20	IO82PPB1
F21	NC
F22	IO84NDB1
G1	IO214NDB3
G2	IO214PDB3
G3	NC
G4	IO222NDB3